

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A thin film transistor substrate with a circuit repair feature in a liquid crystal display, said substrate comprising:

pixel electrodes;

a data lines adjacent to each of two opposed sides of the pixel electrodes for applying a data signals to a the pixel electrodes via a thin film transistors on the substrate;

a gate lines, disposed substantially perpendicular to said data lines for applying a gate signals to the thin film transistors [[,]] an extended portion of said gate line providing; and

a gate dummy patterns parallel to said data lines adjacent to each of two opposed sides of the pixel electrodes and extending substantially the entire length of the pixel electrode portions adjacent and parallel to the data lines to overlap with at least one edge portion of said data lines and an edge portion of the pixel electrodes,

wherein the gate dummy patterns are physically located separate and apart from the gate lines.

2. (Canceled)

3. (Currently Amended) The thin film transistor substrate according to claim 1, wherein when ~~the said~~ a data line is broken, ~~said a~~ gate dummy pattern is used as a redundancy electrode for electrically connecting said broken data line.

4. (Previously Presented) The thin film transistor substrate according to claim 3, wherein said gate dummy pattern includes a recess formed to permit a repair by disconnection of said gate dummy pattern from said gate line.

5. (Currently Amended) The thin film transistor substrate according to claim 1, wherein said at least one gate dummy pattern is used as a black matrix.

6. (Currently Amended) The thin film transistor substrate according to claim 1, further comprising:

a storage capacitor defined by an overlapping part between said at least one gate line and said at least one pixel electrode.

7. (Currently Amended) The thin film transistor substrate according to claim 4, further comprising:

a protrusion protruded from said at least one data line formed in such a manner as to overlap with said recess, thereby shutting off a light leaked between said at least one gate dummy pattern and said at least one gate line.

8. (Currently Amended) The thin film transistor substrate according to claim 1, wherein a gate-insulating layer is formed between said at least one gate dummy pattern and said at least one data line.

9. (Previously Presented) The thin film transistor substrate according to claim 4, wherein said recess is provided at a cutting part for breaking said gate dummy pattern from said gate line in such a manner that said recess is not overlapped with said broken data line.

10. (Currently Amended) A thin film transistor substrate with a circuit repair feature in a liquid crystal display, said substrate comprising:

a pixel electrodes for driving a liquid crystal cells;

a data lines adjacent to each of two opposed sides of the pixel electrode for applying a data signal to said pixel electrode via a thin film transistors on the substrate;

a gate lines disposed substantially perpendicular to said data line for applying a gate signal to the thin film transistors~~[[,]] an extended portion of said gate line providing; and~~

a gate dummy patterns parallel to said data lines adjacent to each of two opposed sides of the pixel electrodes and extending substantially the entire length of the pixel electrode portions adjacent and parallel to the data lines to overlap by about 0.5-1 μm with an edge portion of said data lines and an edge portion of said pixel electrodes, to thereby serve as a black matrix to shut off light leaked between said data lines and said pixel electrodes,

wherein the gate dummy patterns are physically located separate and apart from the gate lines.

11. (Canceled).

12. (Currently Amended) The thin film transistor substrate according to claim 10, wherein when ~~said a~~ data line is broken, ~~said a~~ gate dummy pattern is used as a redundancy electrode for electrically connecting said broken data line.

13. (Previously Presented) The thin film transistor substrate according to claim 12, wherein said gate dummy pattern includes a recess formed to permit a repair by disconnection of said gate dummy pattern from said gate line.

14. (Canceled)

15. (Currently Amended) The thin film transistor substrate according to claim 10, further comprising:

a storage capacitor defined by an overlapping part between ~~said~~ at least one gate line and ~~said~~ at least one pixel electrode.

16. (Previously Presented) The thin film transistor substrate according to claim 13, further comprising:

a protrusion formed in such a manner to overlap with said recess, thereby shutting off a light leaked between said gate dummy pattern and said gate line.

17. (Currently Amended) The thin film transistor substrate according to claim 10, wherein a gate-insulating layer is formed between ~~said~~ at least one gate dummy pattern and ~~said~~ at least one data line.

18. (Previously Presented) The thin film transistor substrate according to claim 13, wherein said recess is provided at a cutting part for breaking said gate dummy pattern from said gate line in such a manner that said recess is not overlapped with said data line.

19-20. (Canceled)

21. (Currently Amended) The thin film transistor substrate according to claim 1, wherein said gate dummy patterns are ~~is~~-formed to cover substantially all of a gap between at least one of the edge portions of said data lines and an edge portion of said pixel electrodes.

22. (Currently Amended) The thin film transistor substrate according to claim 6, wherein an overlap portion of ~~said~~ at least one gate dummy pattern and an edge portion of ~~said~~ at least one

pixel electrode with a gate insulating layer therebetween, forms an auxiliary storage capacitor.

23. (Currently Amended) The thin film transistor substrate according to claim 10, wherein said gate dummy ~~pattern-patterns~~ [[is]] are formed to cover substantially all of a gap between at least one of the edge portions of said data lines and an edge portion of said pixel electrodes.

24. (Currently Amended) The thin film transistor substrate according to claim 15, wherein an overlap portion of ~~said~~ at least one gate dummy pattern and an edge portion of ~~the~~ at least one pixel electrode with a gate insulating layer therebetween, forms an auxiliary storage capacitor.

25-28. (Canceled)